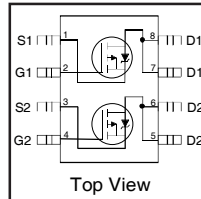


AUIRF7304Q

Features

- Advanced Planar Technology
- Low On-Resistance
- Dual P Channel MOSFET
- Dynamic dV/dT Rating
- Logic Level
- 150°C Operating Temperature
- Fast Switching
- Lead-Free, RoHS Compliant
- Automotive Qualified*

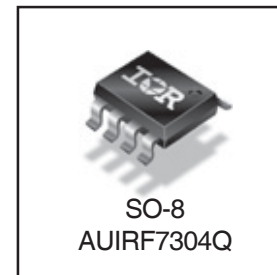


HEXFET® Power MOSFET

$V_{(BR)DSS}$	-20V
$R_{DS(on) \text{ max.}}$	0.090Ω
I_D	-4.3A

Description

Specifically designed for Automotive applications, this cellular design of HEXFET® Power MOSFETs utilizes the latest processing techniques to achieve low on-resistance per silicon area. This benefit combined with the fast switching speed and ruggedized device design that HEXFET power MOSFETs are well known for, provides the designer with an extremely efficient and reliable device for use in Automotive and a wide variety of other applications.



Absolute Maximum Ratings

Stresses beyond those listed under “Absolute Maximum Ratings” may cause permanent damage to the device. These are stress ratings only; and functional operation of the device at these or any other condition beyond those indicated in the specifications is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability. The thermal resistance and power dissipation ratings are measured under board mounted and still air conditions. Ambient temperature (T_A) is 25°C, unless otherwise specified.

	Parameter	Max.	Units
$I_D @ T_A = 25^\circ\text{C}$	10 Sec. Pulsed Drain Current, $V_{GS} @ -4.5\text{V}$	-4.7	A
$I_D @ T_A = 25^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ -4.5\text{V}$	-4.3	
$I_D @ T_A = 70^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ -4.5\text{V}$	-3.4	
I_{DM}	Pulsed Drain Current ①	-17	
$P_D @ T_A = 25^\circ\text{C}$	Power Dissipation ②	2.0	W
	Linear Derating Factor	0.016	W/°C
V_{GS}	Gate-to-Source Voltage	± 12	V
dv/dt	Peak Diode Recovery dv/dt ③	-5.0	V/ns
T_J	Operating Junction and	-55 to + 150	°C
T_{STG}	Storage Temperature Range		

Thermal Resistance

	Parameter	Typ.	Max.	Units
$R_{\theta JA}$	Junction-to-Ambient ④ ⑤	—	62.5	°C/W

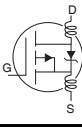
HEXFET® is a registered trademark of International Rectifier.

*Qualification standards can be found at <http://www.irf.com/>

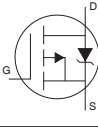
Static Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
V _{(BR)DSS}	Drain-to-Source Breakdown Voltage	-20	—	—	V	V _{GS} = 0V, I _D = -250μA
ΔV _{(BR)DSS} /ΔT _J	Breakdown Voltage Temp. Coefficient	—	-0.012	—	V/°C	Reference to 25°C, I _D = -1mA
R _{DS(on)}	Static Drain-to-Source On-Resistance	—	—	0.090	Ω	V _{GS} = -4.5V, I _D = -2.2A ③
		—	—	0.140		V _{GS} = -2.7V, I _D = -1.8A ③
V _{GS(th)}	Gate Threshold Voltage	-0.70	—	-1.5	V	V _{DS} = V _{GS} , I _D = -250μA
g _{fs}	Forward Transconductance	4.0	—	—	S	V _{DS} = -16V, I _D = -2.2A
I _{bSS}	Drain-to-Source Leakage Current	—	—	-1.0	μA	V _{DS} = -16V, V _{GS} = 0V
		—	—	-25		V _{DS} = -16V, V _{GS} = 0V, T _J = 125°C
I _{GSS}	Gate-to-Source Forward Leakage	—	—	-100	nA	V _{GS} = -12V
	Gate-to-Source Reverse Leakage	—	—	100		V _{GS} = 12V

Dynamic Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
Q _g	Total Gate Charge	—	—	22	nC	I _D = -2.2A
Q _{gs}	Gate-to-Source Charge	—	—	3.3		V _{DS} = -16V
Q _{gd}	Gate-to-Drain ("Miller") Charge	—	—	9.0		V _{GS} = -4.5V, See Fig. 6 & 12③
t _{d(on)}	Turn-On Delay Time	—	8.4	—	ns	V _{DD} = -10V
t _r	Rise Time	—	26	—		I _D = -2.2A
t _{d(off)}	Turn-Off Delay Time	—	51	—		R _G = 6.0Ω
t _f	Fall Time	—	33	—		R _D = 4.5Ω, See Fig. 10 ③
L _D	Internal Drain Inductance	—	4.0	—	nH	Between lead, 6mm (0.25in.) from package and center of die contact
L _S	Internal Source Inductance	—	6.0	—		
C _{iss}	Input Capacitance	—	610	—	pF	V _{GS} = 0V
C _{oss}	Output Capacitance	—	310	—		V _{DS} = -15V
C _{rss}	Reverse Transfer Capacitance	—	170	—		f = 1.0MHz, See Fig. 5

Diode Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I _S	Continuous Source Current (Body Diode)	—	—	-2.5	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I _{SM}	Pulsed Source Current (Body Diode) ①	—	—	-17		
V _{SD}	Diode Forward Voltage	—	—	-1.0	V	T _J = 25°C, I _S = -1.8A, V _{GS} = 0V ③
t _{rr}	Reverse Recovery Time	—	56	84	ns	T _J = 25°C, I _F = -2.2A
Q _{rr}	Reverse Recovery Charge	—	71	110	nC	di/dt = 100A/μs ③
t _{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)				

Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature. (See fig. 11)
- ② I_{SD} ≤ -2.2A, di/dt ≤ -50A/μs, V_{DD} ≤ V_{(BR)DSS}, T_J ≤ 150°C.
- ③ Pulse width ≤ 300μs; duty cycle ≤ 2%.
- ④ Starting T_J = 25°C, R_G = 25Ω, I_{AS} = -2.2A.
- ⑤ When mounted on 1 inch square copper board, t < 10 sec.

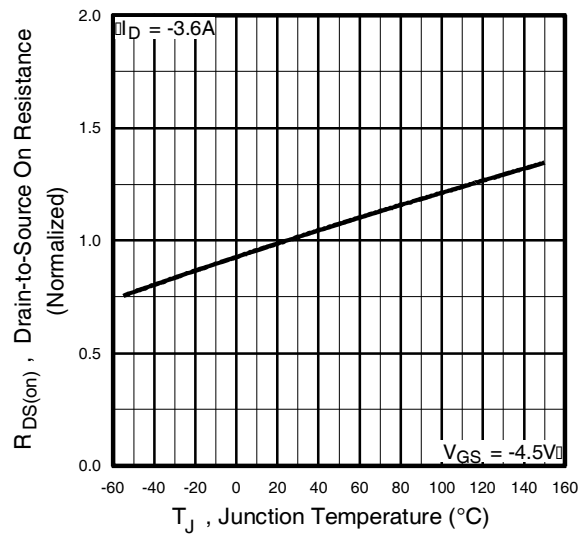
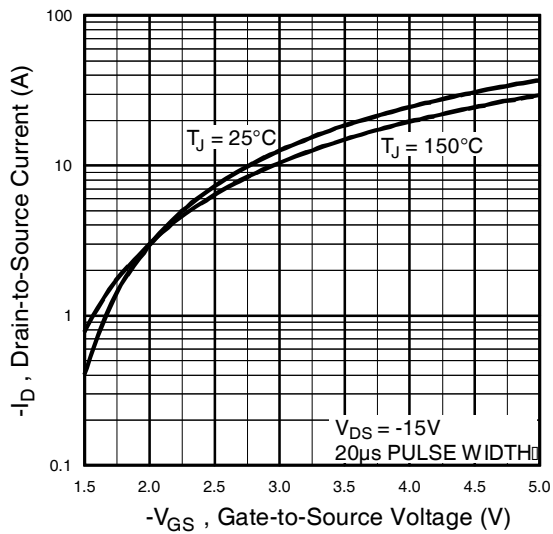
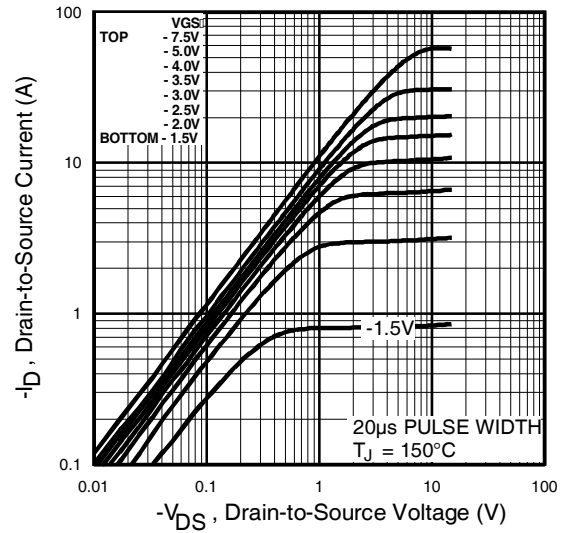
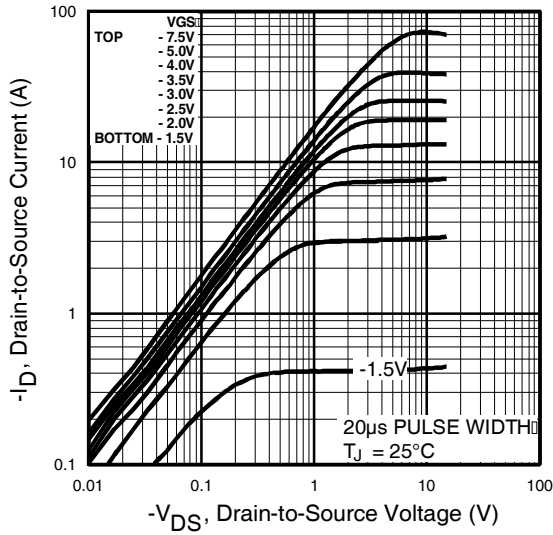
Qualification Information[†]

Qualification Level		Automotive (per AEC-Q101) ^{††}	
		Comments: This part number(s) passed Automotive qualification. IR's Industrial and Consumer qualification level is granted by extension of the higher Automotive level.	
Moisture Sensitivity Level		SO-8	MSL1
ESD	Machine Model	Class M1B (+/- 100V) ^{†††} AEC-Q101-002	
	Human Body Model	Class H0 (+/- 250V) ^{†††} AEC-Q101-001	
	Charged Device Model	Class C5 (+/- 2000V) ^{†††} AEC-Q101-005	
RoHS Compliant		Yes	

† Qualification standards can be found at International Rectifier's web site: <http://www.irf.com/>

†† Exceptions to AEC-Q101 requirements are noted in the qualification report.

††† Highest passing voltage.



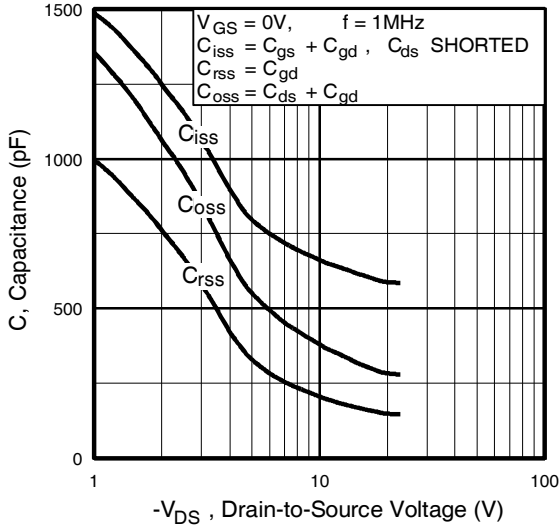


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

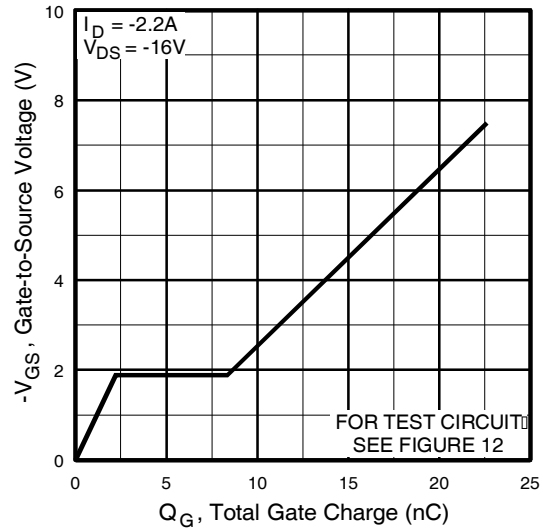


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

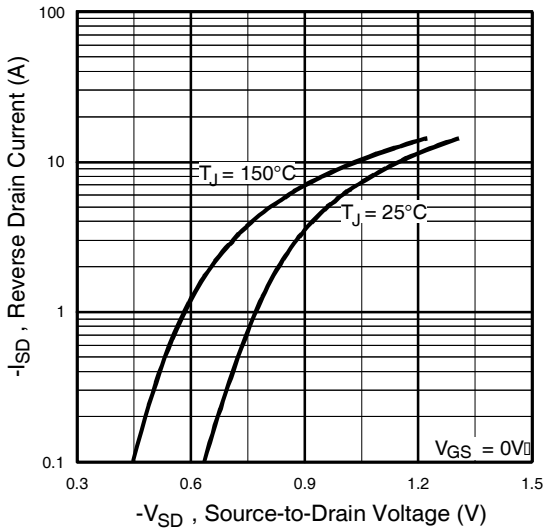


Fig 7. Typical Source-Drain Diode Forward Voltage

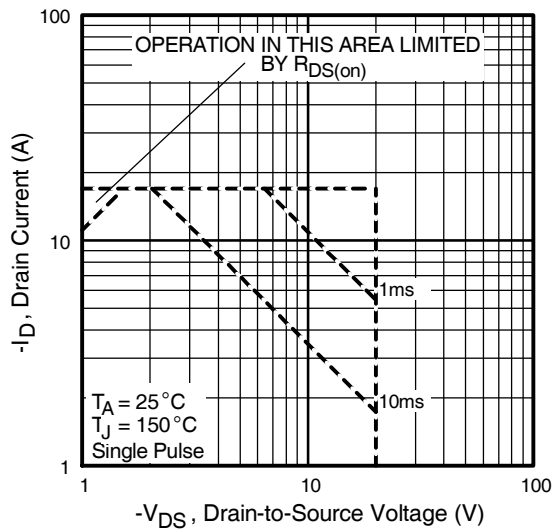


Fig 8. Maximum Safe Operating Area

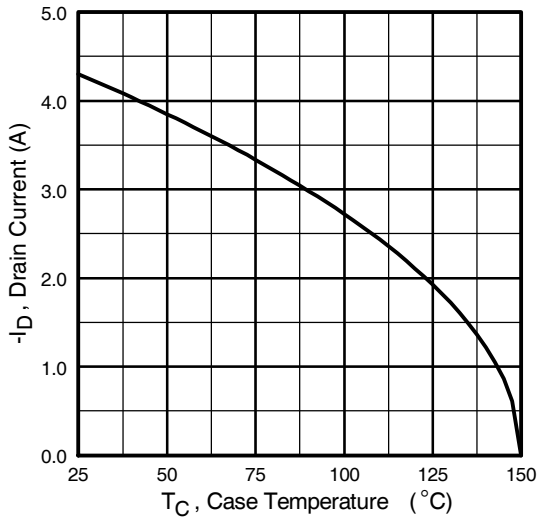


Fig 9. Maximum Drain Current Vs. Ambient Temperature

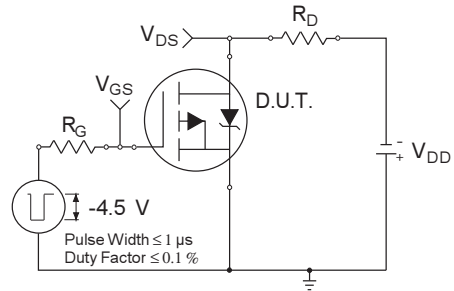


Fig 10a. Switching Time Test Circuit

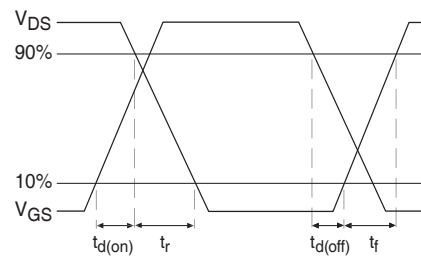


Fig 10b. Switching Time Waveforms

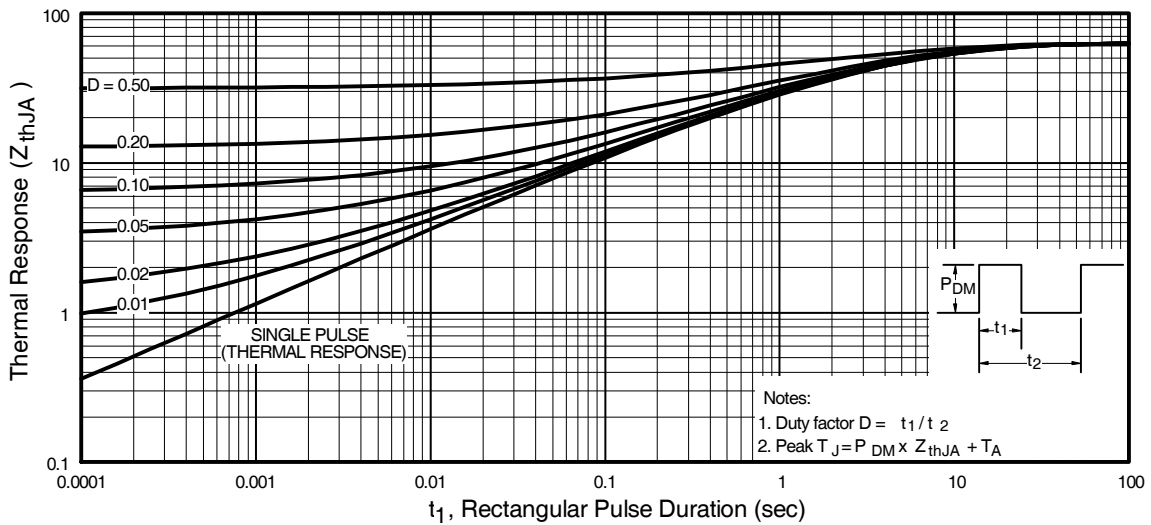


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Ambient

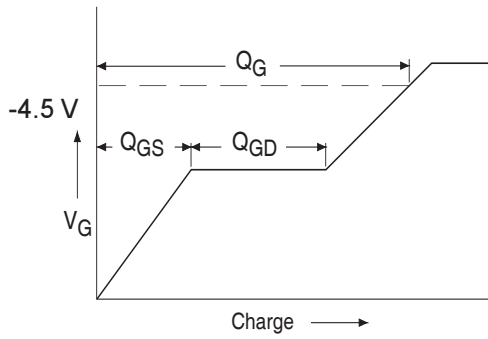


Fig 12a. Basic Gate Charge Waveform

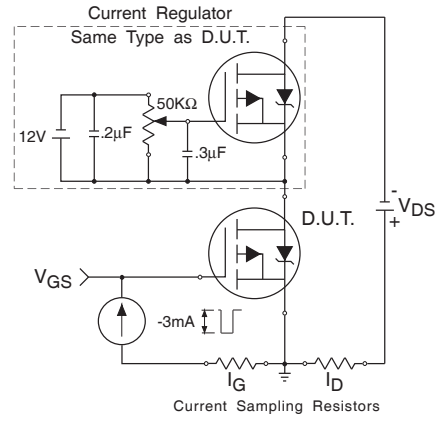
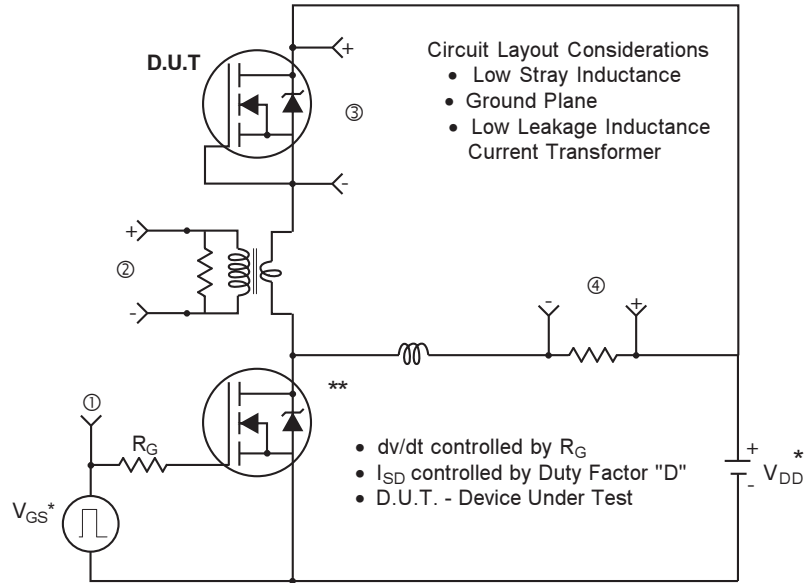


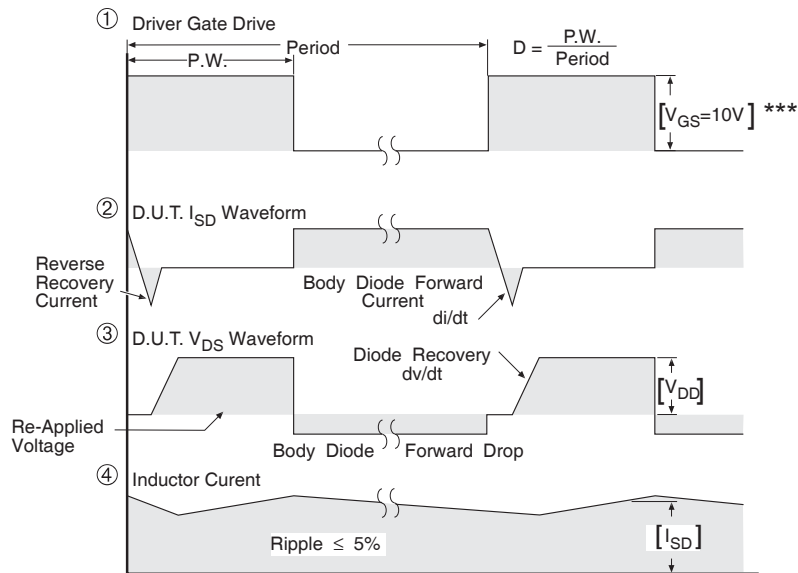
Fig 12b. Gate Charge Test Circuit

Peak Diode Recovery dv/dt Test Circuit



* Reverse Polarity for P-Channel

** Use P-Channel Driver for P-Channel Measurements

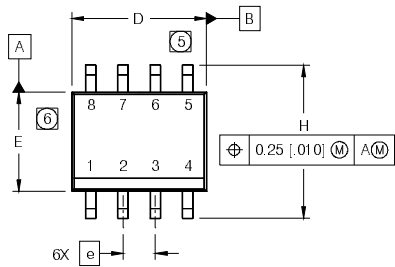


*** $V_{GS} = 5.0V$ for Logic Level and $3V$ Drive Devices

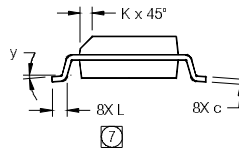
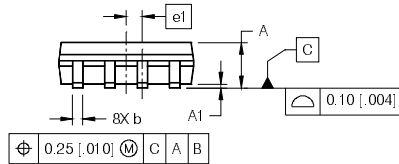
Fig 13. For P-Channel HEXFETS

SO-8 Package Outline

Dimensions are shown in millimeters (inches)



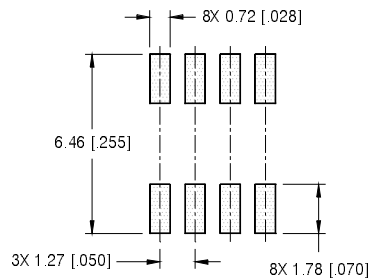
DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.0532	.0688	1.35	1.75
A1	.0040	.0098	0.10	0.25
b	.013	.020	0.33	0.51
c	.0075	.0098	0.19	0.25
D	.189	.1968	4.80	5.00
E	.1497	.1574	3.80	4.00
e	.050 BASIC		1.27 BASIC	
e1	.025 BASIC		0.635 BASIC	
H	.2284	.2440	5.80	6.20
K	.0099	.0196	0.25	0.50
L	.016	.050	0.40	1.27
y	0°	8°	0°	8°



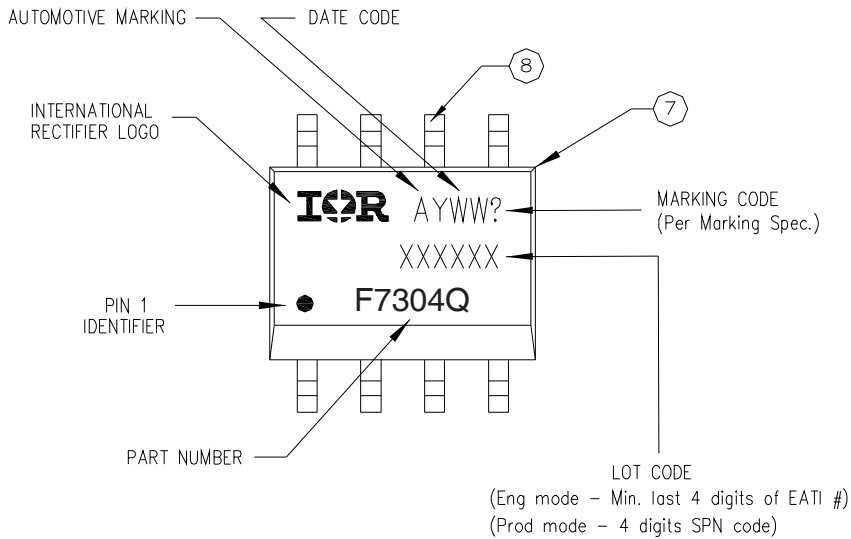
NOTES:

1. DIMENSIONING & TOLERANCING PER ASME Y14.5M-1994.
2. CONTROLLING DIMENSION: MILLIMETER
3. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
4. OUTLINE CONFORMS TO JEDEC OUTLINE MS-012AA.
5. DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS. MOLD PROTRUSIONS NOT TO EXCEED 0.15 [0.006].
6. DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS. MOLD PROTRUSIONS NOT TO EXCEED 0.25 [0.010].
7. DIMENSION IS THE LENGTH OF LEAD FOR SOLDERING TO A SUBSTRATE.

FOOTPRINT



SO-8 Part Marking

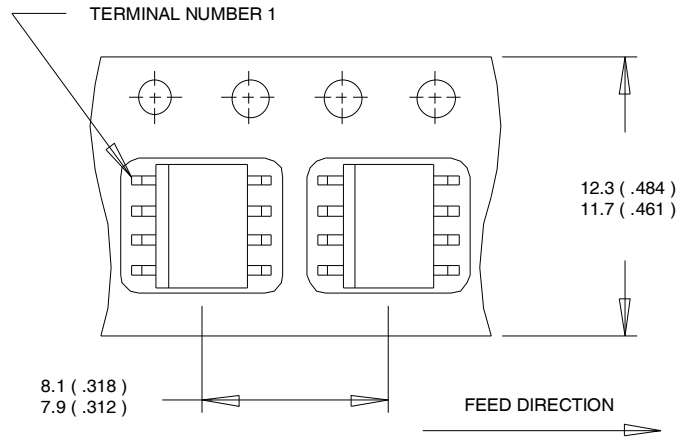


Note: For the most current drawing please refer to IR website at <http://www.irf.com/package/>

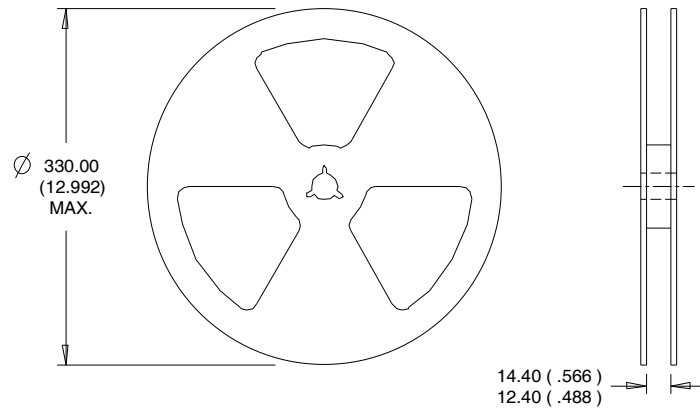
AUIRF7304Q

SO-8 Tape and Reel

Dimensions are shown in millimeters (inches)



- NOTES:
1. CONTROLLING DIMENSION : MILLIMETER.
 2. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS(INCHES).
 3. OUTLINE CONFORMS TO EIA-481 & EIA-541.



- NOTES:
1. CONTROLLING DIMENSION : MILLIMETER.
 2. OUTLINE CONFORMS TO EIA-481 & EIA-541.

Ordering Information

Base part number	Package Type	Standard Pack		Complete Part Number
		Form	Quantity	
AUIRF7304Q	SO-8	Tube	95	AUIRF7304Q
		Tape and Reel	2500	AUIRF7304QTR

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